# 400 mA Low-Drop Voltage **Regulator**

The NCV4276B is a 400 mA output current integrated low dropout regulator family designed for use in harsh automotive environments. It includes wide operating temperature and input voltage ranges. The device is offered with 3.3 V, 5.0 V, and adjustable voltage versions available in 2% output voltage accuracy. It has a high peak input voltage tolerance and reverse input voltage protection. It also provides overcurrent protection, overtemperature protection and inhibit for control of the state of the output voltage. The NCV4276B family is available in DPAK and D<sup>2</sup>PAK surface mount packages. The output is stable over a wide output capacitance and ESR range. The NCV4276B has improved startup behavior during input voltage transients.

## Features

- 3.3 V, 5.0 V, and Adjustable Voltage Version (from 2.5 V to 20 V) ±2% Output Voltage
- 400 mA Output Current
- 500 mV (max) Dropout Voltage (5.0 V Output)
- Inhibit Input
- Very Low Current Consumption
- Fault Protection
  - ◆ +45 V Peak Transient Voltage
  - ♦ -42 V Reverse Voltage
  - Short Circuit
  - Thermal Overload
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These are Pb-Free Devices



# **ON Semiconductor®**

http://onsemi.com



CASE 175AA

**CASE 936A** 

#### MARKING DIAGRAMS



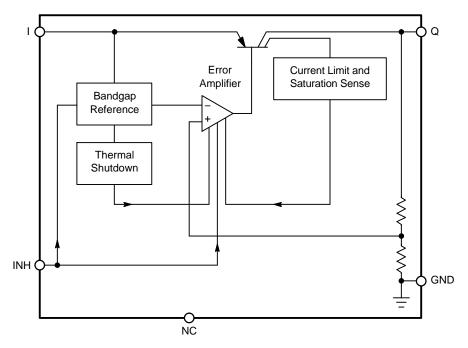


\*Tab is connected to Pin 3 on all packages.

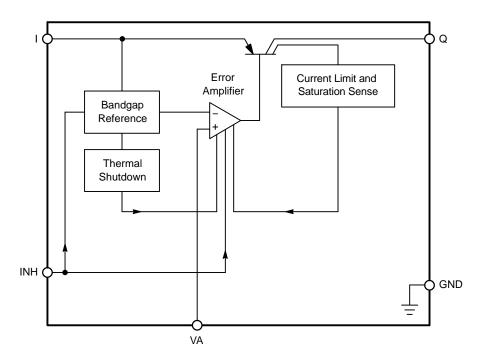
А	= Assembly Location
WL, L	= Wafer Lot
Y	= Year
WW	= Work Week
G	= Pb-Free Device
XX	= 33 (3.3 V)
	= 50 (5.0 V)
	= AJ (Adj. Voltage)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the ordering information section on page 16 of this data sheet.









## **Table 1. PIN FUNCTION DESCRIPTION**

Pin No.	Symbol	Description			
1	I	Input; Battery Supply Input Voltage.			
2	INH	Inhibit; Set low-to inhibit.			
3	GND	Ground; Pin 3 internally connected to heatsink.			
4	NC/VA	Not connected for fixed voltage version/Voltage Adjust Input for adjustable voltage version; use an external voltage divider to set the output voltage			
5	Q	Output: Bypass with a capacitor to GND. See Figures 3 to 7 and Regulator Stability Considerations section.			

#### Table 2. MAXIMUM RATINGS\*

Rating	Symbol	Min	Max	Unit
Input Voltage	VI	-42	45	V
Input Peak Transient Voltage	VI	-	45	V
Inhibit INH Voltage	V <sub>INH</sub>	-42	45	V
Voltage Adjust Input VA	V <sub>VA</sub>	-0.3	10	V
Output Voltage	VQ	-1.0	40	V
Ground Current	Ιq	-	100	mA
Input Voltage Operating Range	VI	V <sub>Q</sub> + 0.5 V or 4.5 V (Note 1)	40	V
ESD Susceptibility (Human Body Model) (Machine Model) (Charged Device Model)		4.0 250 1.25	- - -	kV V kV
Junction Temperature	TJ	-40	150	°C
Storage Temperature	T <sub>stg</sub>	-50	150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

\*During the voltage range which exceeds the maximum tested voltage of I, operation is assured, but not specified. Wider limits may apply. Thermal dissipation must be observed closely.

1. Minimum  $V_I = 4.5 V$  or  $(V_Q + 0.5 V)$ , whichever is higher.

#### Table 3. LEAD TEMPERATURE SOLDERING REFLOW (Note 2)

Lead Temperature Soldering	T <sub>SLD</sub>			°C
Reflow (SMD styles only), Leaded, 60–150 s above 183, 30 s max at peak		-	240	
Reflow (SMD styles only), Lead Free, 60–150 s above 217, 40 s max at peak		-	265	
Wave Solder (through hole styles only), 12 sec max		-	310	

2. Per IPC/JEDEC J-STD-020C.

#### Table 4. THERMAL CHARACTERISTICS (Notes 3 and 4)

Characteristic	Test Conditions (Typical Value)	Unit
DPAK 5-PIN PACKAGE		

	Min Pad Board (Note 5)	1" Pad Board (Note 6)				
Junction-to-Tab (psi-JLx, $\psi_{JLx}$ )	4.2	4.7	C/W			
Junction-to-Ambient ( $R_{\theta JA}, \theta_{JA}$ )	100.9	46.8	C/W			

#### **D<sup>2</sup>PAK 5-PIN PACKAGE**

	0.4 sq. in. Spreader Board (Note 7)	1.2 sq. in. Spreader Board (Note 8)	
Junction-to-Tab (psi-JLx, $\psi_{JLx}$ )	3.8	4.0	C/W
Junction-to-Ambient ( $R_{\theta JA}, \theta_{JA}$ )	74.8	41.6	C/W

3. Minimum V<sub>I</sub> = 4.5 V or (V<sub>Q</sub> + 0.5 V), whichever is higher.

4. Per IPC/JEDEC J-STD-020C.

1 oz. copper, 0.26 inch<sup>2</sup> (168 mm<sup>2</sup>) copper area, 0.062" thick FR4.
 1 oz. copper, 1.14 inch<sup>2</sup> (736 mm<sup>2</sup>) copper area, 0.062" thick FR4.
 1 oz. copper, 0.373 inch<sup>2</sup> (241 mm<sup>2</sup>) copper area, 0.062" thick FR4.
 1 oz. copper, 1.222 inch<sup>2</sup> (788 mm<sup>2</sup>) copper area, 0.062" thick FR4.

Table 5. ELECTRICAL CHARACTERISTICS ( $V_I = 13.5 V_i$ , $-40^{\circ}C < T_J < 150^{\circ}C_i$ ; unless otherwise r	oted.)
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			N	ICV4276	В	
Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
OUTPUT			-			
Output Voltage, 5.0 V Version	VQ	5.0 mA < I <sub>Q</sub> < 400 mA, 6.0 V < V <sub>I</sub> < 28 V	4.9	5.0	5.1	V
Output Voltage, 5.0 V Version	V <sub>Q</sub>	5.0 mA < I <sub>Q</sub> < 200 mA, 6.0 V < V <sub>I</sub> < 40 V	4.9	5.0	5.1	V
Output Voltage, 3.3 V Version	V <sub>Q</sub>	5.0 mA < I <sub>Q</sub> < 400 mA, 4.5 V < V <sub>I</sub> < 28 V	3.234	3.3	3.366	V
Output Voltage, 3.3 V Version	V <sub>Q</sub>	5.0 mA < I <sub>Q</sub> < 200 mA, 4.5 V < V <sub>I</sub> < 40 V	3.234	3.3	3.366	V
Output Voltage, Adjustable Version	AV <sub>Q</sub>	$5.0 \text{ mA} < I_Q < 400 \text{ mA}$ $V_Q+1 < V_I < 40 \text{ V}$ $V_I > 4.5 \text{ V}$	-2%	-	+2%	V
Output Current Limitation	lQ	$V_Q = 90\% V_{QTYP} (V_{QTYP} = 2.5 V \text{ for ADJ Version})$	400	700	1100	mA
Quiescent Current (Sleep Mode) $I_q = I_I - I_Q$	۱ <sub>q</sub>	V <sub>INH</sub> = 0 V	-	-	10	μΑ
Quiescent Current, $I_q = I_I - I_Q$	Ι <sub>q</sub>	I <sub>Q</sub> = 1.0 mA	-	130	200	μΑ
Quiescent Current, $I_q = I_I - I_Q$	Ιq	I <sub>Q</sub> = 250 mA	-	10	15	mA
Quiescent Current, $I_q = I_I - I_Q$	I <sub>q</sub>	I <sub>Q</sub> = 400 mA	-	25	35	mA
Dropout Voltage, Adjustable Version	V <sub>DR</sub>	$I_Q = 250 \text{ mA}, V_{DR} = V_I - V_Q$ V <sub>I</sub> > 4.5 V	_	250	500	mV
Dropout Voltage (5.0 V Version)	V <sub>DR</sub>	I <sub>Q</sub> = 250 mA (Note 9)	_	250	500	mV
Load Regulation	$\Delta V_{Q,LO}$	I <sub>Q</sub> = 5.0 mA to 400 mA	_	3.0	20	mV
Line Regulation	$\Delta V_Q$	$\Delta V_{I} = 12 \text{ V to } 32 \text{ V},$ I <sub>Q</sub> = 5.0 mA	-	4.0	15	mV
Power Supply Ripple Rejection	PSRR	$f_r = 100 \text{ Hz}, V_r = 0.5 \text{ V}_{PP}$	-	70	-	dB
Temperature Output Voltage Drift	d <sub>VQ/dT</sub>	-	-	0.5	-	mV/K
INHIBIT						
Inhibit Voltage, Output High	V <sub>INH</sub>	$V_Q \ge V_{QMIN}$	-	2.3	2.8	V
Inhibit Voltage, Output Low (Off)	V <sub>INH</sub>	$V_Q \le 0.1 V$	1.8	2.2	-	V
Input Current	I <sub>INH</sub>	V <sub>INH</sub> = 5.0 V	5.0	10	20	μΑ
THERMAL SHUTDOWN						
Thermal Shutdown Temperature*	T <sub>SD</sub>	I <sub>Q</sub> = 5.0 mA	150	_	210	°C

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
\*Guaranteed by design, not tested in production.
9. Measured when the output voltage V<sub>Q</sub> has dropped 100 mV from the nominal valued obtained at V = 13.5 V.

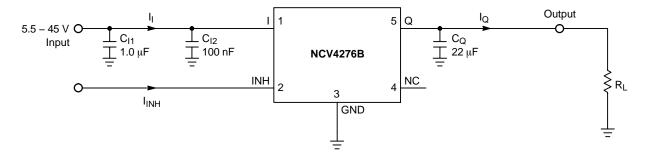
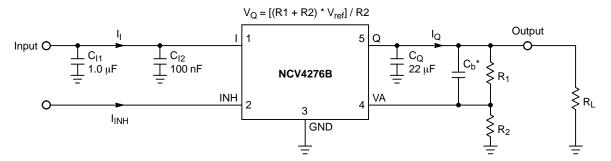


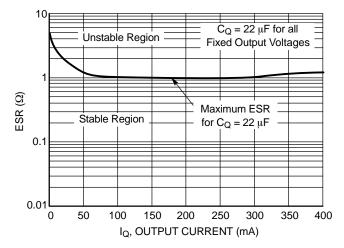
Figure 3. Applications Circuit; Fixed Voltage Version

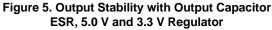


 $C_b^*$  – Required if usage of low ESR output capacitor  $C_Q$  is demand, see Regulator Stability Considerations section

Figure 4. Applications Circuit; Adjustable Voltage Version

## **TYPICAL PERFORMANCE CHARACTERISTICS**





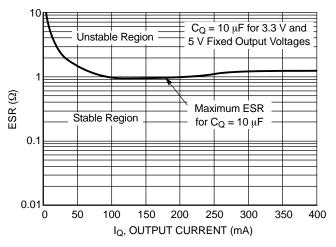
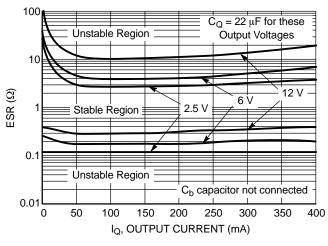
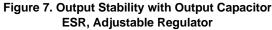
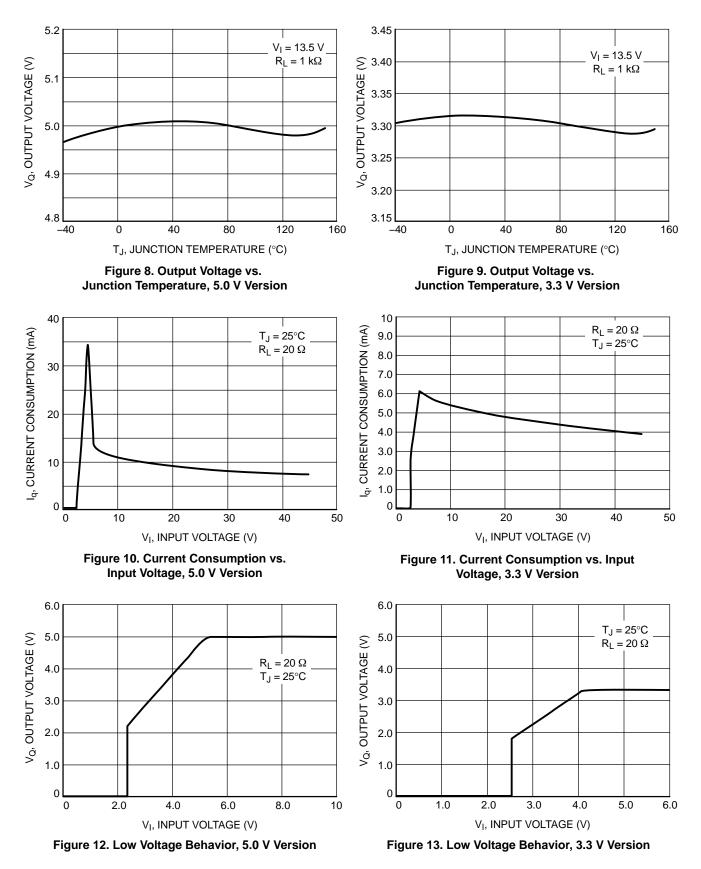


Figure 6. Output Stability with Output Capacitor ESR, 5.0 V and 3.3 V Regulator

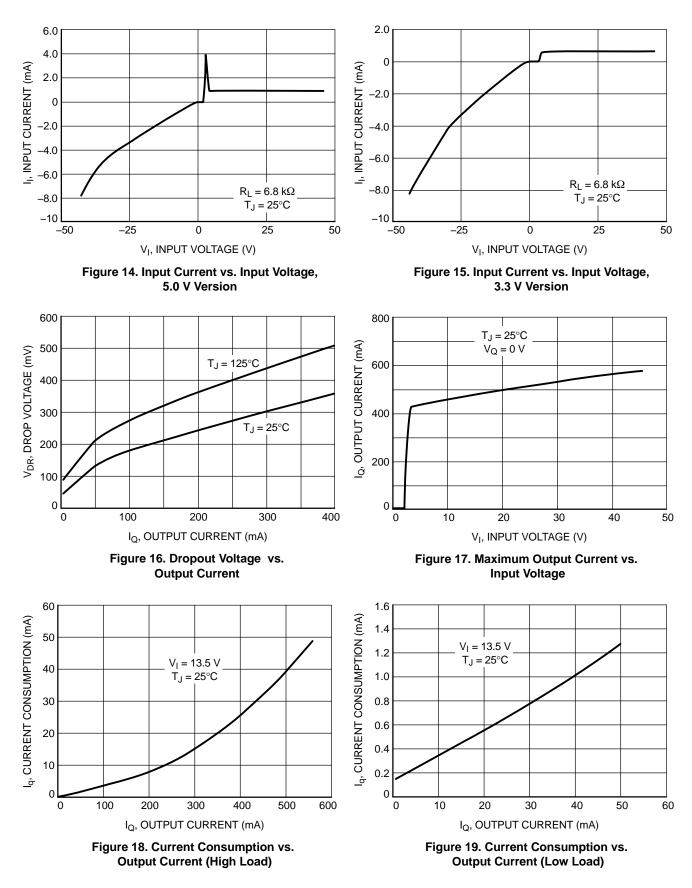




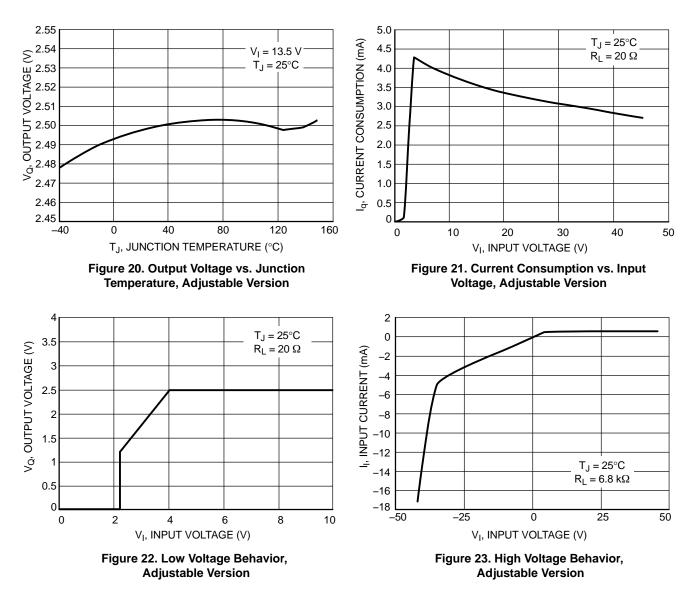


## **TYPICAL PERFORMANCE CHARACTERISTICS – 4276B Version**

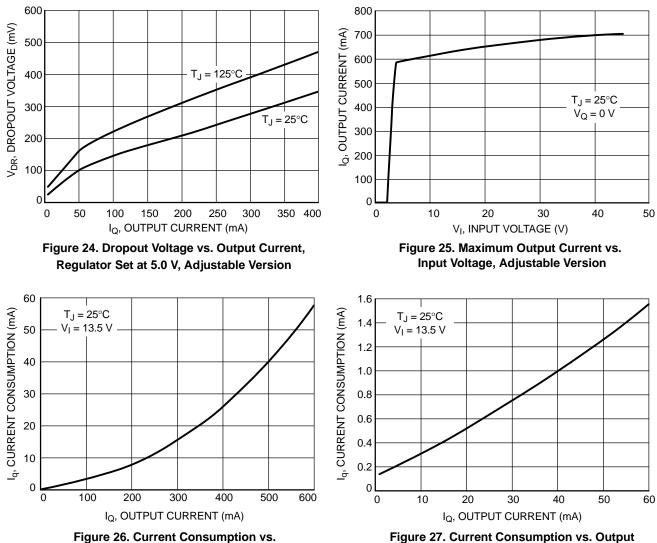




## **TYPICAL PERFORMANCE CHARACTERISTICS – Adjustable Version**



## **TYPICAL PERFORMANCE CHARACTERISTICS – Adjustable Version**



Output Current (High Load), Adjustable Version

Figure 27. Current Consumption vs. Output Current (Low Load), Adjustable Version

## **Circuit Description**

The NCV4276B is an integrated low dropout regulator that provides a regulated voltage at 400 mA to the output. It is enabled with an input to the inhibit pin. The regulator voltage is provided by a PNP pass transistor controlled by an error amplifier with a bandgap reference, which gives it the lowest possible dropout voltage. The output current capability is 400 mA, and the base drive quiescent current is controlled to prevent oversaturation when the input voltage is low or when the output is overloaded. The regulator is protected by both current limit and thermal shutdown. Thermal shutdown occurs above 150°C to protect the IC during overloads and extreme ambient temperatures.

#### Regulator

The error amplifier compares the reference voltage to a sample of the output voltage  $(V_Q)$  and drives the base of a PNP series pass transistor via a buffer. The reference is a bandgap design to give it a temperature-stable output. Saturation control of the PNP is a function of the load current and input voltage. Oversaturation of the output power device is prevented, and quiescent current in the ground pin is minimized. See Figure 4, Test Circuit, for circuit element nomenclature illustration.

## **Regulator Stability Considerations**

The input capacitors ( $C_{I1}$  and  $C_{I2}$ ) are necessary to stabilize the input impedance to avoid voltage line influences. Using a resistor of approximately 1.0  $\Omega$  in series with  $C_{I2}$  can stop potential oscillations caused by stray inductance and capacitance.

The output capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability. The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures ( $-25^{\circ}$ C to  $-40^{\circ}$ C), both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor  $C_Q$ , shown in Figure 3, should work for most applications; see also Figures 5 to 7 for output stability at various load and Output Capacitor ESR conditions. Stable region of ESR in Figures 5 to 7 shows ESR values at which the LDO output voltage does not have any permanent oscillations at any dynamic changes of output load current. Marginal ESR is the value at which the output voltage waving is fully damped during four periods after the load change and no oscillation is further observable.

ESR characteristics were measured with ceramic capacitors and additional series resistors to emulate ESR. Low duty cycle pulse load current technique has been used to maintain junction temperature close to ambient temperature.

Minimum ESR for  $C_Q = 22 \ \mu$ F is native ESR of ceramic capacitor with which the fixed output voltage devices are performing stable. Murata ceramic capacitors were used,

GRM32ER71C226KE18 (22 μF, 16 V, X7R, 1210), GRM31CR71C106KAC7 (10 μF, 16 V, X7R, 1206).

## **Calculating Bypass Capacitor**

If usage of low ESR ceramic capacitors is demand in case of Adjustable Regulator, connect the bypass capacitor  $C_b$  between Voltage Adjust pin and Q pin according to Applications circuit at Figure 4.

Parallel combination of bypass capacitor  $C_b$  with the feedback resistor  $R_1$  contributes in the device transfer function as an additional zero and affects the device loop stability, therefore its value must be optimized. Attention to the Output Capacitor value and its ESR must be paid. See also Stability in High Speed Linear LDO Regulators Application Note, AND8037/D for more information.

Optimal value of bypass capacitor is given by following expression

$$C_b = \frac{1}{2 \times \pi \times f_Z \times R_1} \cdot (F) \qquad (eq. 1)$$

where

 $R_1$  = the upper feedback resistor

 $f_z$  = the frequency of the zero added into the device transfer function by  $R_1$  and  $C_b$  external components.

Set the  $R_1$  resistor according to output voltage requirement. Chose the  $f_z$  with regard on the output capacitance  $C_Q$ , refer to the table below.

C <sub>Q</sub> (μF)	10	22	47	100
f <sub>z</sub> Range (kHz)	20 - 50	14 - 35	10 - 20	7 – 14

Ceramic capacitors and its part numbers listed bellow have been used as low ESR output capacitors  $C_Q$  from the table above to define the frequency ranges of additional zero required for stability.

GRM31CR71C106KAC7 (10 μF, 16 V, X7R, 1206) GRM32ER71C226KE18 (22 μF, 16 V, X7R, 1210) GRM32ER61C476ME15 (47 μF, 16 V, X5R, 1210) GRM32ER60J107ME20 (100 μF, 6.3 V, X5R, 1210)

## Inhibit Input

The inhibit pin is used to turn the regulator on or off. By holding the pin down to a voltage less than 1.8 V, the output of the regulator will be turned off. When the voltage on the Inhibit pin is greater than 2.8 V, the output of the regulator will be enabled to power its output to the regulated output voltage. The inhibit pin may be connected directly to the input pin to give constant enable to the output regulator.

## Setting the Output Voltage (Adjustable Version)

The output voltage range of the adjustable version can be set between 2.5 V and 20 V. This is accomplished with an external resistor divider feeding back the voltage to the IC back to the error amplifier by the voltage adjust pin VA. The internal reference voltage is set to a temperature stable reference of 2.5 V.

The output voltage is calculated from the following formula. Ignoring the bias current into the VA pin:

$$V_Q = [(R1 + R2) * V_{ref}] / R2$$
 (eq. 2)

Use R2 < 50 k to avoid significant voltage output errors due to VA bias current.

Connecting VA directly to Q without R1 and R2 creates an output voltage of 2.5 V.

Designers should consider the tolerance of R1 and R2 during the design phase.

The input voltage range for operation (pin 1) of the adjustable version is between ( $V_Q + 0.5 V$ ) and 40 V. Internal bias requirements dictate a minimum input voltage of 4.5 V. The dropout voltage for output voltages less than 4.0 V is (4.5 V –  $V_O$ ).

#### Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 28) is:

$$PD(max) = [VI(max) - VQ(min)]IQ(max) + + VI(max)Iq$$
(eq. 3)

where:

V <sub>I(max)</sub>	is the maximum input voltage,
V <sub>Q(min)</sub>	is the minimum output voltage,
I <sub>Q(max)</sub>	is the maximum output current for the
	application,
Iq	is the quiescent current the regulator
-	consumes at $I_{O(max)}$ .

Once the value of  $P_{D(max)}$  is known, the maximum permissible value of  $R_{\theta JA}$  can be calculated:

$$R_{\theta}JA = \frac{150^{\circ}C - T_A}{P_D} \qquad (eq. 4)$$

The value of  $R_{\theta JA}$  can then be compared with those in the package section of the data sheet. Those packages with  $R_{\theta JA}$  less than the calculated value in Equation 4 will keep the die temperature below 150°C.

In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heatsink will be required.

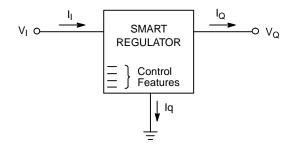


Figure 28. Single Output Regulator with Key Performance Parameters Labeled

#### Heatsinks

A heatsink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of  $R_{\theta JA}$ :

$$R_{\theta}JA = R_{\theta}JC + R_{\theta}CS + R_{\theta}SA \qquad (eq. 5)$$

where:

 $R_{\theta JC}$  is the junction-to-case thermal resistance,  $R_{\theta CS}$  is the case-to-heatsink thermal resistance,  $R_{\theta SA}$  is the heatsink-to-ambient thermal resistance.

 $R_{\theta JC}$  appears in the package section of the data sheet. Like  $R_{\theta JA}$ , it too is a function of package type.  $R_{\theta CS}$  and  $R_{\theta SA}$  are functions of the package type, heatsink and the interface between them. These values appear in data sheets of heatsink manufacturers.

Thermal, mounting, and heatsinking considerations are discussed in the ON Semiconductor application note AN1040/D.

#### **Thermal Model**

See pages 13 to 16 for detailed information about thermal model parameters.

Drain Co	opper Area (1	oz thick)	168 mm <sup>2</sup>	736 mm <sup>2</sup>		168 mm <sup>2</sup>	736 mm <sup>2</sup>	
(SPI	ICE Deck For	mat)	Cauer I	Network		Foster	Network	
			168 mm <sup>2</sup>	736 mm <sup>2</sup>	Units	Tau	Tau	Units
C_C1	Junction	GND	1.00E-06	1.00E-06	W-s/C	1.36E-08	1.361E-08	sec
C_C2	node1	GND	1.00E-05	1.00E-05	W-s/C	7.41E-07	7.411E-07	sec
C_C3	node2	GND	6.00E-05	6.00E-05	W-s/C	1.04E-05	1.029E-05	sec
C_C4	node3	GND	1.00E-04	1.00E-04	W-s/C	3.91E-05	3.737E-05	sec
C_C5	node4	GND	4.36E-04	3.64E-04	W-s/C	1.80E-03	1.376E-03	sec
C_C6	node5	GND	6.77E-02	1.92E-02	W-s/C	3.77E-01	2.851E-02	sec
C_C7	node6	GND	1.51E–01	1.27E-01	W-s/C	3.79E+00	9.475E-01	sec
C_C8	node7	GND	4.80E-01	1.018	W-s/C	2.65E+01	1.173E+01	sec
C_C9	node8	GND	3.740	2.955	W-s/C	8.71E+01	8.59E+01	sec
C_C10	node9	GND	10.322	0.438	W-s/C			sec
			168 mm <sup>2</sup>	736 mm <sup>2</sup>		R's	R's	
R_R1	Junction	node1	0.015	0.015	C/W	0.0123	0.0123	C/W
R_R2	node1	node2	0.08	0.08	C/W	0.0585	0.0585	C/W
R_R3	node2	node3	0.4	0.4	C/W	0.0304	0.0287	C/W
R_R4	node3	node4	0.2	0.2	C/W	0.3997	0.3772	C/W
R_R5	node4	node5	2.97519	2.6171	C/W	3.115	2.68	C/W
R_R6	node5	node6	8.2971	1.6778	C/W	3.571	1.38	C/W
R_R7	node6	node7	25.9805	7.4246	C/W	12.851	5.92	C/W
R_R8	node7	node8	46.5192	14.9320	C/W	35.471	7.39	C/W
R_R9	node8	node9	17.7808	19.2560	C/W	46.741	28.94	C/W
R_R10	node9	GND	0.1	0.1758	C/W			C/W

NOTE: Bold face items represent the package without the external thermal system.

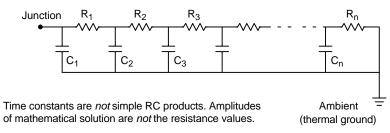


Figure 29. Grounded Capacitor Thermal Network ("Cauer" Ladder)

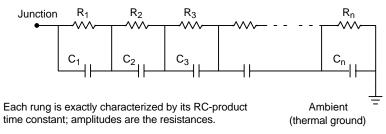


Figure 30. Non-Grounded Capacitor Thermal Ladder ("Foster" Ladder)

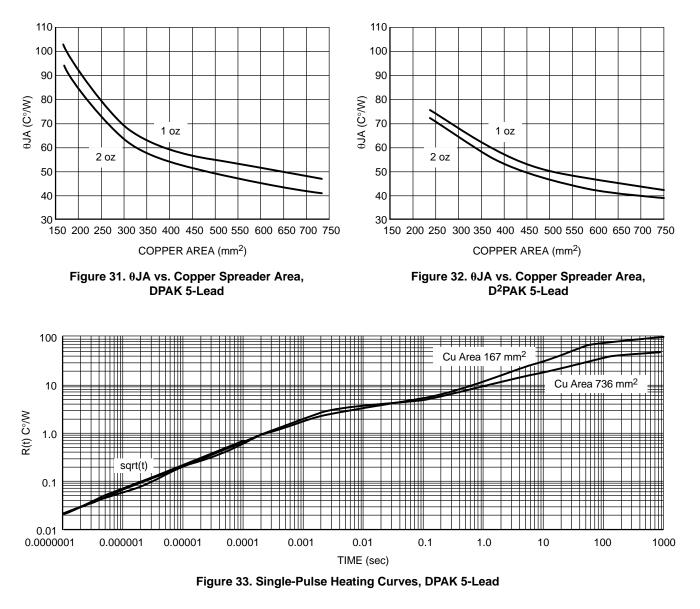
Drain Copper Area (1 oz thick)		241 mm <sup>2</sup>	788 mm <sup>2</sup>		241 mm <sup>2</sup>	788 mm <sup>2</sup>		
(SPICE Deck Format)		Cauer I	Network		Foster Network			
			241 mm <sup>2</sup>	653 mm <sup>2</sup>	Units	Tau	Tau	Units
C_C1	Junction	GND	1.00E-06	1.00E-06	W-s/C	1.361E-08	1.361E-08	sec
C_C2	node1	GND	1.00E-05	1.00E-05	W-s/C	7.411E-07	7.411E-07	sec
C_C3	node2	GND	6.00E-05	6.00E-05	W-s/C	1.005E-05	1.007E-05	sec
C_C4	node3	GND	1.00E-04	1.00E-04	W-s/C	3.460E-05	3.480E-05	sec
C_C5	node4	GND	2.82E-04	2.87E-04	W-s/C	7.868E-04	8.107E-04	sec
C_C6	node5	GND	5.58E-03	5.95E-03	W-s/C	7.431E-03	7.830E-03	sec
C_C7	node6	GND	4.25E-01	4.61E-01	W-s/C	2.786E+00	2.012E+00	sec
C_C8	node7	GND	9.22E-01	2.05	W-s/C	2.014E+01	2.601E+01	sec
C_C9	node8	GND	1.73	4.88	W-s/C	1.134E+02	1.218E+02	sec
C_C10	node9	GND	7.12	1.31	W-s/C			sec
			241 mm <sup>2</sup>	653 mm <sup>2</sup>		R's	R's	
R_R1	Junction	node1	0.015	0.0150	C/W	0.0123	0.0123	C/W
R_R2	node1	node2	0.08	0.0800	C/W	0.0585	0.0585	C/W
R_R3	node2	node3	0.4	0.4000	C/W	0.0257	0.0260	C/W
R_R4	node3	node4	0.2	0.2000	C/W	0.3413	0.3438	C/W
R_R5	node4	node5	1.85638	1.8839	C/W	1.77	1.81	C/W
R_R6	node5	node6	1.23672	1.2272	C/W	1.54	1.52	C/W
R_R7	node6	node7	9.81541	5.3383	C/W	4.13	3.46	C/W
R_R8	node7	node8	33.1868	18.9591	C/W	6.27	5.03	C/W
R_R9	node8	node9	27.0263	13.3369	C/W	60.80	29.30	C/W
R_R10	node9	GND	1.13944	0.1191	C/W			C/W

NOTE: Bold face items represent the package without the external thermal system.

The Cauer networks generally have physical significance and may be divided between nodes to separate thermal behavior due to one portion of the network from another. The Foster networks, though when sorted by time constant (as above) bear a rough correlation with the Cauer networks, are really only convenient mathematical models. Cauer networks can be easily implemented using circuit

simulating tools, whereas Foster networks may be more easily implemented using mathematical tools (for instance, in a spreadsheet program), according to the following formula:

$$R(t) = \sum_{i=1}^{n} R_{i}(1 - e^{-t/tau_{i}})$$
 (eq. 6)



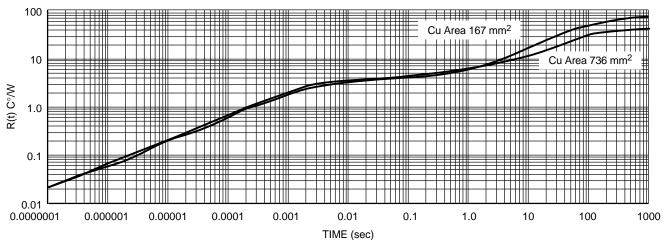
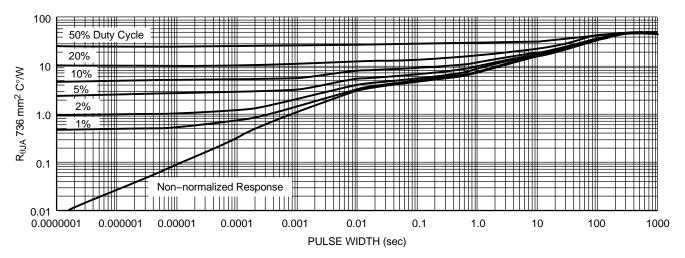


Figure 34. Single-Pulse Heating Curves, D<sup>2</sup>PAK 5-Lead





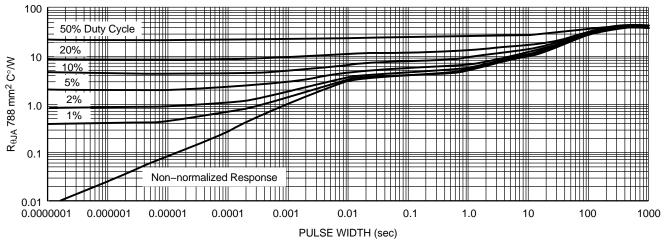


Figure 36. Duty Cycle for 1" Spreader Boards, D<sup>2</sup>PAK 5-Lead

Table 8. ORDERING INFORMATION					
Device	Output Voltage Accuracy	Output Voltage	Package	Shipping <sup>†</sup>	
NCV4276BDT33RKG	2%	2.2.1	DPAK, 5-Pin (Pb-Free)	2,500 / Tape & Reel	
NCV4276BDS33R4G		3.3 V	D <sup>2</sup> PAK, 5-Pin (Pb-Free)	800 / Tape & Reel	
NCV4276BDT50RKG		5.0 V	DPAK, 5-Pin (Pb-Free)	2,500 / Tape & Reel	
NCV4276BDS50R4G			D <sup>2</sup> PAK, 5-Pin (Pb-Free)	800 / Tape & Reel	
NCV4276BDTADJRKG		Adiustable	DPAK, 5-Pin (Pb-Free)	2,500 / Tape & Reel	
NCV4276BDSADJR4G		Adjustable	D <sup>2</sup> PAK, 5-Pin (Pb-Free)	800 / Tape & Reel	

## 

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

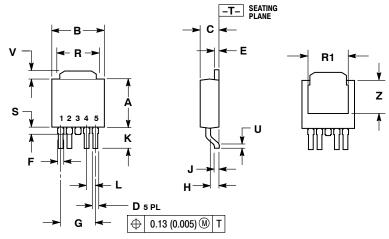




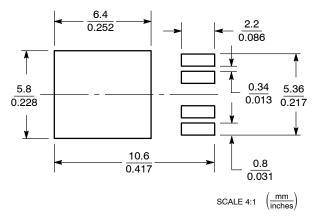
**DPAK-5, CENTER LEAD CROP** CASE 175AA **ISSUE B** 

DATE 15 MAY 2014

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#### RECOMMENDED SOLDERING FOOTPRINT\*

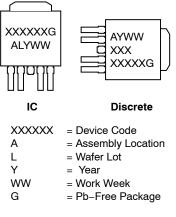


\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.235	0.245	5.97	6.22		
в	0.250	0.265	6.35	6.73		
С	0.086	0.094	2.19	2.38		
D	0.020	0.028	0.51	0.71		
Е	0.018	0.023	0.46	0.58		
F	0.024	0.032	0.61	0.81		
G	0.180 BSC		4.56 BSC			
н	0.034	0.040	0.87	1.01		
J	0.018	0.023	0.46	0.58		
К	0.102	0.114	2.60	2.89		
L	0.045 BSC 1.14 BSC		BSC			
R	0.170	0.190	4.32	4.83		
<b>R</b> 1	0.185	0.210	4.70	5.33		
S	0.025	0.040	0.63	1.01		
U	0.020		0.51			
v	0.035 0.050		0.89	1.27		
Z	0.155	0.170	3.93	4.32		

#### GENERIC **MARKING DIAGRAMS\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " .", may or may not be present.

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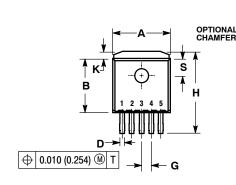


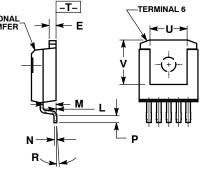


D<sup>2</sup>PAK 5-LEAD CASE 936A-02 **ISSUE D** 

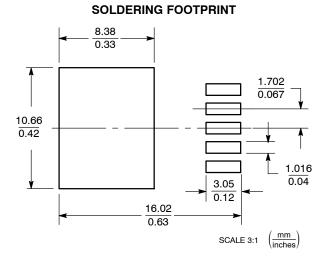
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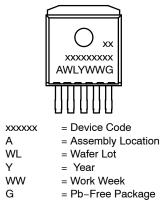


NOTES:

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- 4.
- AND K. DIMENSIONS U AND V ESTABLISH A MINIMUM MOUNTING SURFACE FOR TERMINAL 6. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 5. (0.635) MAXIMUM.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.386	0.403	9.804	10.236	
В	0.356	0.368	9.042	9.347	
С	0.170	0.180	4.318	4.572	
D	0.026	0.036	0.660	0.914	
Е	0.045 0.055		1.143	1.397	
G	0.067 BSC		1.702 BSC		
Н	0.539	0.579	13.691	14.707	
К	0.050	REF	1.270 REF		
L	0.000	0.010	0.000	0.254	
М	0.088	0.102	2.235	2.591	
Ν	0.018	0.026	0.457	0.660	
Р	0.058	0.078	1.473	1.981	
R	0 °	8°	0 °	8°	
S	0.116 REF		2.946	6 REF	
U	0.200 MIN		5.080 MIN		
v	0.250 MIN		6.350 MIN		

#### GENERIC **MARKING DIAGRAM\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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